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PATENT ABSTRACTS OF JAPAN

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(71)Applicant : HITACHI LTD

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(54) SEMICONDUCTOR DEVICE

(57)Abstract:

PURPOSE: How to fabricate a semiconductor volatile memory FET of storage mechanism in silicon nitride film, the fabrication of which is simple and high integration and high speed motion of which are also possible.

<http://www19.ipdl.inpit.go.jp/PA1/result/detail/main/wAAAEhayUjDA351150980P...> 2010/12/02